

List of figures

Chapter 2

- Fig. 1 The secondary ion mass spectrometry result and the TRIM-calculated excess Si-atom density in multi-energy Si-ion-implanted $\text{SiO}_2:\text{Si}^+$ sample as a function of implanting depth. 30
- Fig. 2 PL spectra of the $\text{SiO}_2:\text{Si}^+/\text{Si}$ samples at (a) as-implanted condition, or annealed at 1100°C for (b) 30, (c) 60, (d) 180 and (e) 240 min. The inset figure plots the PL spectra of (1) n-type Si substrate (2) 60-min annealed n-type Si substrate (3) SiO_2/Si sample (4) 60-min annealed SiO_2/Si sample and (5) as-implanted substrate. 30
- Fig. 3 Wavelength evolution of three PL peaks in $\text{SiO}_2:\text{Si}^+$ samples as-implanted or annealed at 1100°C for different annealing times. 31
- Fig. 4 The annealing-time dependent PL intensities at different wavelengths of 415 nm, 455 nm, and 520 nm. 31
- Fig. 5 C–V hysteresis measurement of MOS diode made on (a) as-implanted $\text{SiO}_2:\text{Si}^+$ and (b) $\text{SiO}_2:\text{Si}^+$ annealed at 1100°C for 3 h. The inset figure shows the NOV defect concentration as a function of annealing time obtained from C–V analysis. 32
- Fig. 6 Normalized TRPL spectra of $\text{SiO}_2:\text{Si}^+$ samples at (a) as-implanted condition, or annealed at 1100°C for (b) 1.5 h, (c) 3 h and (d) 4 h. 32
- Fig. 7 EPR spectra of the $\text{SiO}_2:\text{Si}^+$ samples at as-implanted condition, and annealed at 1100°C for 45, 90 and 180 min. 33
- Fig. 8 TRPL lifetime and concentrations of NOV and E'_δ defects in $\text{SiO}_2:\text{Si}^+$ at different annealing times. 33
- Fig. 9 CW and pulsed current-voltage measurements of Ag/ $\text{SiO}_2:\text{Si}^+/\text{n-Si}/\text{Ag}$ MOS diode with $\text{SiO}_2:\text{Si}^+$ annealing at 1100°C for 180 min. 34
- Fig. 10 The average EL power as a function of pulsed current and voltage. The inset figure shows CW (dashed line) and pulsed (dotted line) current-voltage responses of Ag/ $\text{SiO}_2:\text{Si}^+/\text{n-Si}/\text{Ag}$ MOS diode with $\text{SiO}_2:\text{Si}^+$ annealing at 1100°C for 3hrs. 34
- Fig. 11 Lifetime testing of Ag/ $\text{SiO}_2:\text{Si}^+/\text{n-Si}/\text{Ag}$ MOS diode under pulsed-current EL operation. The inset figure plots the operating condition of the MOS diode and its EL pattern at bias of 3 A. 35
- Fig. 12 Pulsed EL power as a function of the bias current. The inset figure is the lifetime and decaying rate of the Ag/ $\text{SiO}_2:\text{Si}^+/\text{n-Si}/\text{Ag}$ MOS diode under pulsed-current EL operation. 35

Fig. 13	EL patterns at different bias currents of 0.35 A (left), 1.25 A (middle) and 3 A (right).	36
Fig. 14	EL spectra of the Ag/SiO ₂ :Si ⁺ /n-Si/Ag MOS diode at different bias currents of 0.35 (dash line), 1.25 (dot line) and 3 A (solid line).	36
Fig. 15	Energy band diagrams of the Ag/SiO ₂ :Si ⁺ /n-Si/Ag structure with metal-oxide barrier potential of $\phi_m = 3.28$ V under reverse bias at 3.7 V (left part) and 5.7 V (right part). Three defect-related irradiative emissions at (a) 415 nm from the WOB defect, (b) 455 nm from the NOV defect and (c) 520 nm from the E' ₈ defect.	37

Chapter 3

Fig. 1	PL spectra of 3-h-annealed Si-rich SiO _x films fabricated by PECVD with different N ₂ O/SiH ₄ ratios. The inset shows the peak intensity as a function of the N ₂ O/SiH ₄ ratio.	83
Fig. 2	Room-temperature PL spectra of annealed Si-rich SiO _x films fabricated by PECVD with different substrate temperatures from 100 to 350°C. The inset shows the peak intensity as a function of substrate temperature.	83
Fig. 3	PL spectra of as-grown sample A7 after annealing at 1100 °C for 1-5 h.	84
Fig. 4	Peak PL intensities of NOV defect and nc-Si, and peak wavelength of nc-Si as a function of the annealing time.	84
Fig. 5	Time-resolved PL traces of sample A7 after annealing at 1100 °C for 1, 2, and 3 h.	85
Fig. 6	PL intensity and peak wavelength as a function of N ₂ O fluence.	85
Fig. 7	TRPL spectra of nc-Si embedded in PECVD-grown SiO _x samples for different annealing time.	86
Fig. 8	Planar-view HRTEM picture of 15 min-annealed PECVD-grown SiO _x film	86
Fig. 9	Size distribution of nc-Si in the 15 min-annealed PECVD-grown SiO _x film	87
Fig. 10	PL spectra of PECVD-grown SiO _x samples annealed from 15 to 60 min.	87
Fig. 11	Density and size distribution of nc-Si buried in annealed SiO _x film as a function of annealing time.	88
Fig. 12	PL as function of annealing time at different process pressures.	88
Fig. 13	EELS spectra of pure Si, as-grown SiO _x and 30 min-annealed samples.	89

Fig. 14	PL intensity and peak wavelength as a function of substrate temperature.	89
Fig. 15	EL spectra of samples prepared under different substrate temperatures.	90
Fig. 16	EL patterns of ITO/SiO _x :nc-Si/p-Si/Al MOSLED.	90
Fig. 17	I-V and P-I curves of ITO/SiO _x :nc-Si/p-Si/Al MOSLED.	91
Fig. 18	Plot of $\ln(J_G/E^2)$ as a function of $1/E$ for three ITO/SiO _x :nc-Si/p-Si/Al MOSLEDs with their SiO _x grown at (a) 300, (b) 350 and (c) 400°C. Inset: Band structure of ITO/SiO _x :nc-Si/p-Si MOSLED.	91
Fig. 19	Internal and external quantum efficiencies as a function of substrate temperature.	92
Fig. 20	Direct tunneling mechanism of MOS diode	92
Fig. 21	Plot of $\ln(J)$ as a function of voltage for three different ITO/SiO _x :nc-Si/p-Si/Al MOSLEDs with their SiO _x grown at 300, 350 and 400°C and a simulated direct tunneling current (solid line).	93
Fig. 22	Fowler-Nordheim tunneling mechanism of MOS diode.	93
Fig. 23	Thermionic emission tunneling mechanism of MOS diode.	94
Fig. 24	Plot of $\ln(J)$ as a function of voltage for three ITO/SiO _x :nc-Si/p-Si/Al MOSLEDs with their SiO _x grown at 300, 350 and 400°C and a simulated thermionic current.	94
Fig. 25	Poole-Frenkel tunneling mechanism of MOS diode.	95
Fig. 26	Plot of $\ln(J/E)$ as a function of $E^{0.5}$ for three ITO/SiO _x :nc-Si/p-Si/Al MOSLEDs with their SiO _x grown at 300, 350 and 400°C and a simulated Poole Frankel tunneling current.	95
Fig. 27	Images of SiO _{1.25} film after CO ₂ laser annealing at P_{laser} increasing from 3 to 13.5 kW/cm ² .	96
Fig. 28	The thicknesses of annealed SiO _{1.25} films as a function of annealing time.	96
Fig. 29	Ablation thickness of SiO _x as a function of P_{laser} . Inset: PL spectra of CO ₂ laser annealed SiO _{1.25} films at P_{laser} = (a)1.5 (b)3 (c)4.5 (d)6 (e)7.5 (f)9 (g)10.5 kW/cm ² .	97
Fig. 30	RBS spectrum of the as-grown SiO _{1.25} film on a Si substrate.	97
Fig. 31	Cross-sectional HRTEM images of SiO _x CO ₂ -laser-annealed at P_{laser} = 6 kW/cm ² . Inset: the electron diffraction pattern (lower right) of a (111)-plane Si nanocrystal (lower left).	98
Fig. 32	Transmission spectra of Quartz, as-PECVD grown SiO _{1.25} film and the CO ₂ laser annealed SiO _{1.25} film at P_{laser} = 6 kW/cm ² .	98

- Fig. 33 Transmission spectra of CO₂ laser annealed SiO_{1.25} films at P_{laser} increasing from 6 to 12 kW/cm². 99
- Fig. 34 Reflectance spectra of the quartz substrate, as-PECVD grown SiO_{1.25} film and the CO₂ laser annealed SiO_{1.25} film at $P_{laser} = 6$ kW/cm². 99
- Fig. 35 Reflectance spectra of CO₂ laser annealed SiO_{1.25} films at P_{laser} increasing from 6 to 12 kW/cm². 100
- Fig. 36 Refractive index of CO₂ laser annealed SiO_{1.25} film as a function of P_{laser} . 100
- Fig. 37 PL spectra of CO₂ laser annealed SiO_x at (a) 6 kW/cm², (b) furnace-annealing at 1100°C for 30 min and CO₂ laser annealed SiO_x at (c) 12 kW/cm². 101
- Fig. 38 Plot of $\ln(J_G/E^2)$ as a function of $1/E$ for CO₂ laser-annealed and furnace-annealed MOSLEDs. 101
- Fig. 39 P-I curves of (a) ITO/ CO₂ laser RTA SiO_x /p-Si/Al and (b) ITO/ furnace-annealed SiO_x /p-Si/Al MOSLEDs. Inset: Energy band diagram of a highly forward biased ITO/ CO₂ laser RTA SiO_x /p-Si/Al MOSLED. 102
- Fig. 40 EL spectra of MOSLEDs made by CO₂ laser RTA (lower) and furnace-annealed (upper) SiO_x. Inset: EL patterns of CO₂ laser RTA (lower) and furnace-annealed (upper) MOSLEDs. 102

Chapter 4

- Fig. 1 Cross-sectional HRTEM photographs and corresponding electron diffraction patterns of Si-rich SiO_x grown at ICP powers of 45 (upper left) and 35 (lower left) watts. (a) The cross-sectional TEM photograph of the SiO_x film PECVD grown at normal ICP power. Inset: the electron diffraction pattern of the PECVD-grown SiO_x film. (b) and (c): the lattice parameter and orientation of the Si nanocrystals in PECVD-grown SiO_x film. (d) The cross-sectional TEM photograph of Si-rich SiO_x film with dense interfacial Si nano-pyramids grown at threshold ICP power. (e) The magnified cross-sectional TEM photograph of the Si-nano-pyramid embedded Si-rich SiO_x/Si interface. (f) The magnified TEM photograph for a single Si nano-pyramid and its electron diffraction pattern shown in the inset. (g): The observed orientations for the Si nano-pyramid (upper part) and Si substrate (lower part). (h) and (i): the orientation of the Si nanocrystals in the PECVD-grown Si-rich SiO_x film at threshold ICP-power condition. 127

Fig. 2	The plots of $\ln(I/E^2)$ as a function of $1/E$ for three MOSLED samples with their SiO_x films PECVD grown at different ICP powers.	128
Fig. 3	Threshold F-N tunneling electric field as a function of the area density of Si nano-pyramids.	128
Fig. 4	The energy band diagrams of a highly biased MOSLEDs using SiO_x grown at different PECVD conditions. Left: the SiO_x grown at normal ICP power without Si nano-pyramids but with dense interfacial radiant defects. Right: the SiO_x grown at threshold ICP power with Si nano-pyramids at the SiO_x/Si interface.	129
Fig. 5	The I-V and I-P curves of the ITO/ SiO_x /p-Si/Al MOSLEDs with SiO_x films grown at different ICP powers. Upper: ICP power of 45 W. Middle: ICP power of 40 W. Lower: ICP power of 30 W.	129
Fig. 6	TEM images of nc-Si within the annealed SiO_x film grown without (left) and with (right) interfacial Si nano-pyramids.	130
Fig. 7	EL spectra of ITO/ SiO_x /p-Si/Al MOSLEDs with (solid) or without (dashed) interfacial Si nano-pyramids.	130
Fig. 8	EL patterns of three MOSLED samples without (upper) and with Si-nano-pyramid concentrations of $\rho=10^9/\text{cm}^2$ (middle) and $\rho=10^{11}/\text{cm}^2$ (lower).	131
Fig. 9	Output power stability of three MOSLED samples with different Si-nano-pyramid concentrations.	131
Fig. 10	SEM image of Ni nano-dots precipitated from the evaporated Ni film on SiO_2/Si with different film thickness.	132
Fig. 11	SEM image of Si nano-pillars formed after ICP-RIE with different RF/Bias power recipes.	132
Fig. 12	Density and average diameter of Si nano-pillars on Si substrate as a function of RF/Bias power ratio in ICP-RIE system	133
Fig. 13	(a) Micro-PL spectrum of as-made Si nano-pillar array. (b) Normalized PL spectra of unprocessed pure Si wafer and etched Si nano-pillar. (c) Si nano-pillar related PL and pure Si PL spectrum. (d) PL spectra of etched Si nano-pillars.	133
Fig. 14	Peak wavelength of Si nano-pillar as a function of rod size. Inset: Plan-view SEM picture of etched Si nano-pillars.	134
Fig. 15	(a) SEM image of Ni nano-dots precipitated from the evaporated Ni film on SiO_2/Si . (b) SEM image of Si nano-pillars formed after ICP-RIE with RF/Bias power recipe of 50/100W. (c) Device structure of a silicon nanocrystal based MOSLED on Si nano-pillar array. (d) An ITO/ SiO_x /Si/Al diode with a circular contact diameter	134

of 0.8 mm.

Fig. 16 Normalized PL spectra of nc-Si based MOSLEDs (a) without and 135
(b)with Si nano-pillars. Normalized EL spectra of nc-Si based
MOSLEDs (c) with and (d) without Si nano-pillars.

Fig. 17 I-V and I-P curves of nc-Si based MOSLEDs with/without Si 135
nano-pillars. Inset: EL pattern of nc-Si based MOSLED with Si
nano-pillars.

Fig. 18 The ratio of the EL power from nc-Si MOSLED made on Si 136
nano-pillar to that made on smooth Si wafer at different biased
current.

